

Continental Device India Limited

An ISO/TS16949 and ISO 9001 Certified Company



SOT-23 Formed SMD Package

CMBTA42 CMBTA43

SILICON EPITAXIAL TRANSISTORS

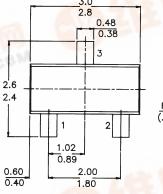
N-P-N transistors

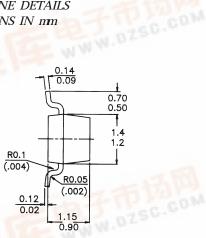
Marking

CMBTA42 = 1D

CMBTA43 = 1E

PACKAGE OUTLINE DETAILS ALL DIMENSIONS IN mm





Pin configuration

1 = BASE

2 = EMITTER 3 = COLLECTOR



2

ABSOLUTE MAXIMUM RATINGS

		CMBTA42		A43			
Collector-base voltage (open emitter)	V_{CBO}	max.	300		200 V		
Collector-emitter voltage (open base)	V_{CEO}	max.	300	. He	200 V		
Emitter-base voltage (open collector)	V_{EBO}	max.		6	V		
Collector current (d.c.)	I_C	max.		500	mA		
Total power dissipation up to $T_{amb} = 25 ^{\circ}C$	P _{tot}	max.		250	mW		
Junction temperature	T_{j}	max.		<i>150</i>	$^{\circ}$ C		
D.C. current gain							
$I_C = 10 \text{ mA}; V_{CE} = 10 \text{ V}$	h_{FE}	min.		40			
Transition frequency at $f = 35$ MHz							
$I_C = 10 \text{ mA}; V_{CE} = 20 \text{ V}$	f_T	min.		<i>50</i>	MHz		
Feedback capacitance at $f = 1$ MHz							
$I_C = 0; \ V_{CE} = 20 \ V$	C_{re}	max.	3		<u>4</u> pF		



CMBTA42 CMBTA43

RATINGS (at $T_A = 25$ °C unless otherwise specimiting values	ecified)					
Collector-base voltage (open emitter)	V_{CBO}	max.	300	ı	200	V
Collector-emitter voltage (open base)	VCBO $VCEO$	max.			200	
Emitter-base voltage (open collector)		max.	300	6	200	V
Collector current (d.c.)	V_{EBO}	max.		500		v mA
, ,	I_C			250		mW
Total power dissipation up to $T_{amb} = 25$ °C	P_{tot}	max.	5.5	230 to +1	50	° C
Storage temperature	T_{Stg}	may	-33	150	30	$^{\circ}C$
Junction temperature	T_j	max.		150		C
THERMAL CHARACTERISTICS						
$T_j = P (R_{th j-t} + R_{th t-s} + R_{th s-a}) + T_{amb}$ Thermal resistance						
from junction to ambient	$R_{th\ j-a}$	=		<i>500</i>		K/W
CHARACTERISTICS (at $T_A = 25^{\circ}C$ unless of	herwise spe	cified)				
Collector-emitter breakdown voltage		СМВ	TA 42		A43	
$I_C = 1 \text{ mA}; I_B = 0$	V _{(BR)CEO}	min.	300		200	V
Collector-base breakdown voltage	. ,					
$I_C = 100 \ \mu A; I_E = 0$	V _(BR) CBO	min.	300		200	V
Emitter-base breakdown voltage	, ,					
$I_E = 100 \ \mu A; I_C = 0$	$V_{(BR)EBO}$	min.		6		V
Collector cut-off current						
$I_E = 0; \ V_{CB} = 200 \ V$	I_{CBO}	max.	0.1		-	μA
$I_E = 0; \ V_{CB} = 160 \ V$	I_{CBO}	max.	-		0.1	μA
Emitter cut-off current						
$I_C = 0; \ V_{BE} = 6 \ V$	I_{EBO}	max.	0.1		-	μA
$I_C = 0$; $V_{BE} = 4 V$	I_{EBO}	max.	-		0.1	μA
Feedback capacitance at $f = 1$ MHz						
$I_E = 0; \ V_{CB} = 20 \ V$	C_{re}	max.	3		4	рF
Saturation voltages						
$I_C = 20 \text{ mA}$; $I_B = 2 \text{ mA}$	V_{CEsat}	max.		0.5		V
$I_C = 20 \text{ mA}; I_B = 2 \text{ mA}$	V_{BEsat}	max.		0.9		V
D.C. current gain						
$I_C = 1 \text{ mA}; V_{CE} = 10 \text{ V}$	h_{FE}	min.		25		
$I_C = 10 \text{ mA}; V_{CE} = 10 \text{ V}$	h_{FE}	min.		40		
$I_C = 30 \text{ mA}; V_{CE} = 10 \text{ V}$	h_{FE}	min.		40		
Transition frequency at $f = 35$ MHz						
$I_C = 10 \text{ mA; } V_{CE} = 20 \text{ V}$	f_T	min.		<i>50</i>		MHz

Customer Notes

Disclaimer

The product information and the selection guides facilitate selection of the CDIL's Discrete Semiconductor Device(s) best suited for application in your product(s) as per your requirement. It is recommended that you completely review our Data Sheet(s) so as to confirm that the Device(s) meet functionality parameters for your application. The information furnished on the CDIL Web Site/CD are believed to be accurate and reliable. CDIL however, does not assume responsibility for inaccuracies or incomplete information. Furthermore, CDIL does not assume liability whatsoever, arising out of the application or use of any CDIL product; neither does it convey any license under its patent rights nor rights of others. These products are not designed for use in life saving/support appliances or systems. CDIL customers selling these products (either as individual Discrete Semiconductor Devices or incorporated in their end products), in any life saving/support appliances or systems or applications do so at their own risk and CDIL will not be responsible for any damages resulting from such sale(s).

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